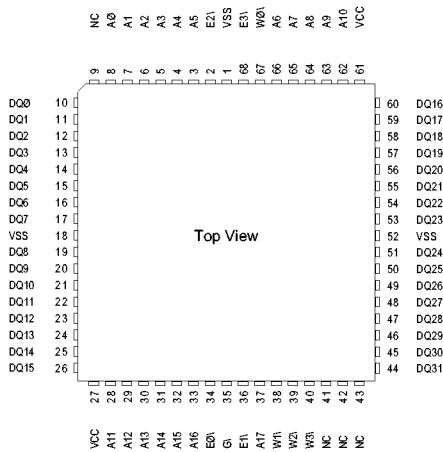


**ADVANCED**

**Features**

- 256Kx32 bit CMOS Static  
 Random Access Memory Array
- Fast Access Times: 12, 15 and 20ns
  - Individual Byte Enables
  - User Configurable Organization with Minimal Additional Logic
  - Master Output Enable and Write Control
  - TTL Compatible Inputs and Outputs
  - Fully Static, No Clocks
- Surface Mount Package
- 68 Lead PLCC, No. 99
  - Small Footprint, 0.990 Sq. In.
  - Multiple Ground Pins for Maximum Noise Immunity
- Single 3.3V (±5%) Supply Operation

**Pin Configurations and Block Diagram**



**Pin Names**

A0-A17	Address Inputs
E0-E3	Chip Enables
W0-W3	Write Enable
G	Output Enable
DQ0-DQ31	Data Input/Output
VCC	Power (3.3V±5%)
VSS	Ground
NC	No Connect

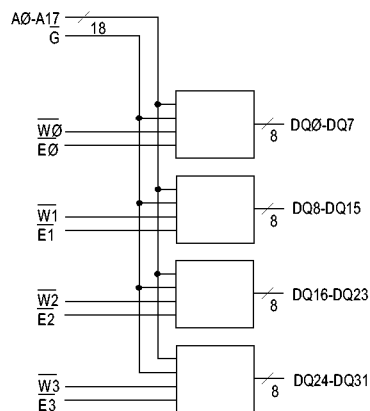
**256Kx32 CMOS High Speed  
 Static RAM**

The EDI8LM32257V is a high-speed 8-Megabit static RAM device with access times of 12, 15 and 20ns over the Commercial, Industrial and Military temperature range. The device allows the user to capitalize on the cost advantages of a plastic component while not sacrificing all of the reliability available in a full military component.

Extended temperature testing is performed using the same test patterns as those used on EDI's ceramic military product line. EDI fully characterizes the devices to determine the proper test patterns required for testing at the temperature extremes. This is a critical process, since the operating characteristics of the devices change when they are operated beyond the commercial temperature range. Users of EDI's ruggedized plastic components will benefit from EDI's extensive experience in characterizing SRAMs for use in military systems.

The EDI8LM32257V can also be used as a direct replacement for EDI's ceramic 68-pin JLCC product, the EDI8C32128CA or the plastic EDI8LM32129C. The plastic product provides 50% in weight reduction on 50% savings in capacitance loading. The EDI8LM32257V also provides a cost effective alternative for COTs programs.

**NOTE: Solder Reflow temperature should not exceed 260°C for 10 seconds.**



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### Absolute Maximum Ratings\*

Voltage on any pin relative to VSS	-0.5V to 4.6V
Operating Temperature TA (Ambient)	
Commercial	0°C to +70°C
Industrial	-40°C to +85°C
Military	-55°C to +125°C
Storage Temperature	-55°C to +150°C
Power Dissipation	2 Watts
Output Current	20 mA
Junction Temperature, TJ	175°C

\*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

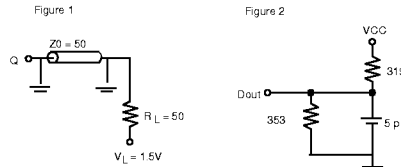
### Recommended DC Operating Conditions

Parameter	Sym	Min	Typ	Max	Units
Supply Voltage	VCC	3.135	3.3	3.465	V
Supply Voltage	VSS	0	0	0	V
Input High Voltage	VIH	2.2	--	VCC+0.3	V
Input Low Voltage	VIL	-0.3	--	0.8	V

### AC Test Conditions

Input Pulse Levels	VSS to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Levels	1.5V
Output Load	Figure 1

(note: For TEHQZ,TGHQZ and TWLQZ, see figure 2)



### DC Electrical Characteristics

Parameter	Sym	Conditions	Min	Max	Units	
Operating Power Supply Current	ICC1	W= VIL, I/O = 0mA, Min Cycle	12	15	20 ns mA	
Standby (TTL) Supply Current	ICC2	$\bar{E} \geq V_{IH}$ , $V_{IN} - V_{IL}$ or $V_{IN} \leq V_{IH}$ , $f = 0$ MHz	100	100	100	mA
Full Standby Supply Current	ICC3	$\bar{E} \geq V_{CC} - 0.2V$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	20	20	20	mA
Input Leakage Current	ILI	$V_{IN} = 0V$ to VCC	$\pm 10$	$\pm 10$	$\pm 10$	$\mu A$
Output Leakage Current	ILO	$V_{I/O} = 0V$ to VCC	$\pm 10$	$\pm 10$	$\pm 10$	$\mu A$
Output High Voltage	VOH	IOH = -4.0mA	2.4			V
Output Low Voltage	VOL	IOL = 8.0mA	0.4	0.4	0.4	V

### Truth Table

$\bar{E}$	$\bar{W}$	$\bar{G}$	BS0-3	Mode	Output	Power
H	X	X	X	Standby	High Z	ICC2, ICC3
L	H	H	X	Output Disable	High Z	ICC1
L	X	X	H	Output Disable	High Z	ICC1
L	H	L	L	Read	DOUT	ICC1
L	L	X	L	Write	DIN	ICC1

X Means Don't Care

### Capacitance

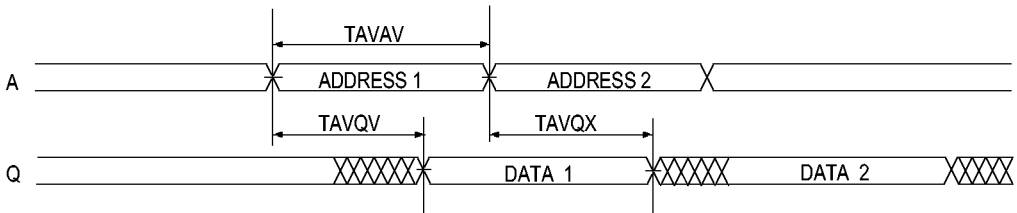
(f=1.0MHz, VIN=VCC or VSS)

Parameter	Sym	Max	Unit
Address Lines	CA	20	pF
Data Lines	CD/Q	10	pF
Write & Output Enable Lines	$\bar{W}$ , $\bar{G}$	6	pF
Chip Enable Lines/Byte Select	$\bar{E}$ , BS	9	pF

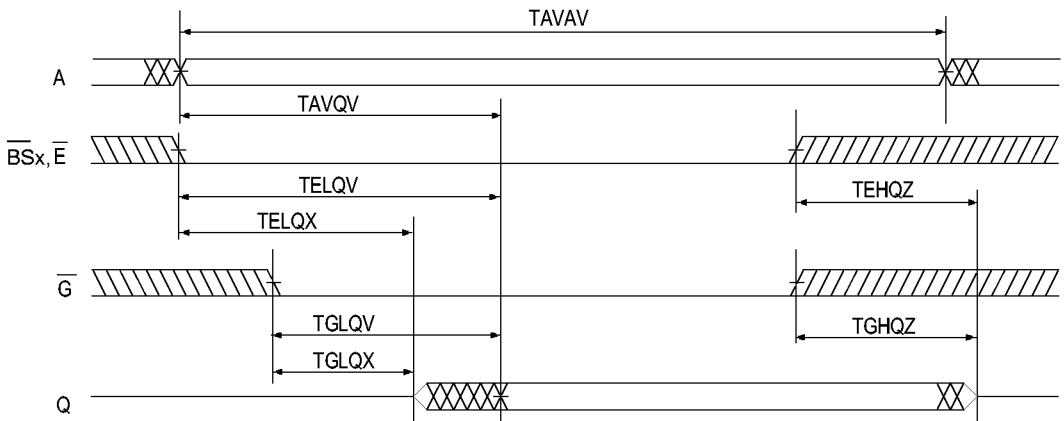
**AC Characteristics Read Cycle**

Parameter	Symbol		12ns		15ns		20ns	
	JEDEC	Alt.	Min	Max	Min	Max	Min	Max
Read Cycle Time	TAVAV	TRC	12		15		20	ns
Address Access Time	TAVQV	TAA		12		15		20 ns
Chip Enable Access Time	TELQV	TACS		12		15		20 ns
Byte Select Access Time	TBLQX	TBLZ		12		15		20 ns
Chip Enable to Output in Low Z (1)	TELQX	TCLZ	3		3		3	ns
Byte Select to Output in Low Z	TBLQX	TBLZ	3		3		3	ns
Chip Disable to Output in High Z (1)	TEHQZ	TCHZ		7		8		10 ns
Byte Select to Output in High Z	TBHQZ	TBHZ		7		8		10 ns
Output Hold from Address Change	TAVQX	TOH	3		3		3	ns
Output Enable to Output Valid	TGLQV	TOE		5		6		10 ns
Output Enable to Output in Low Z (1)	TGLQX	TOLZ	2		2		2	ns
Output Disable to Output in High Z(1)	TGHQZ	TOHZ		4		5		8 ns

**Read Cycle 1 - W High, G, E Low**



**Read Cycle 2 - W High**

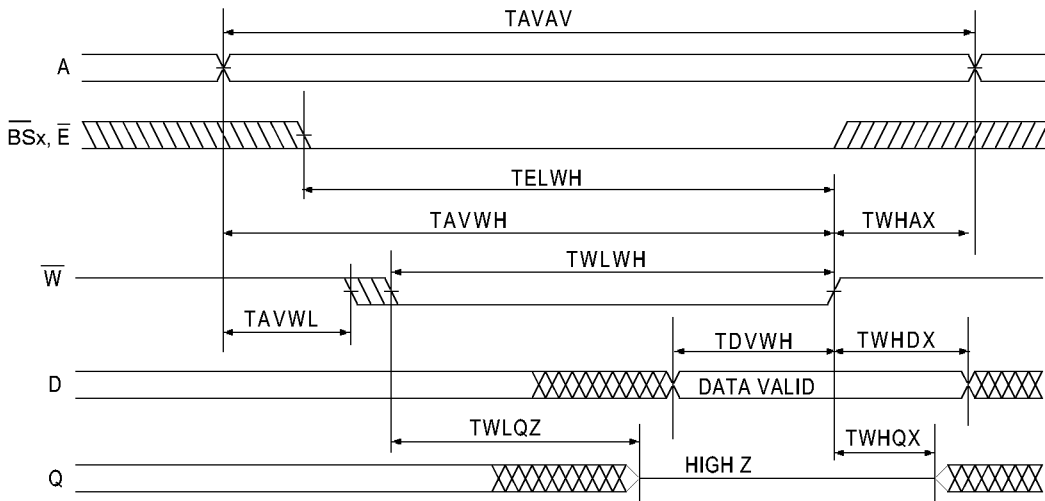


### AC Characteristics Write Cycle

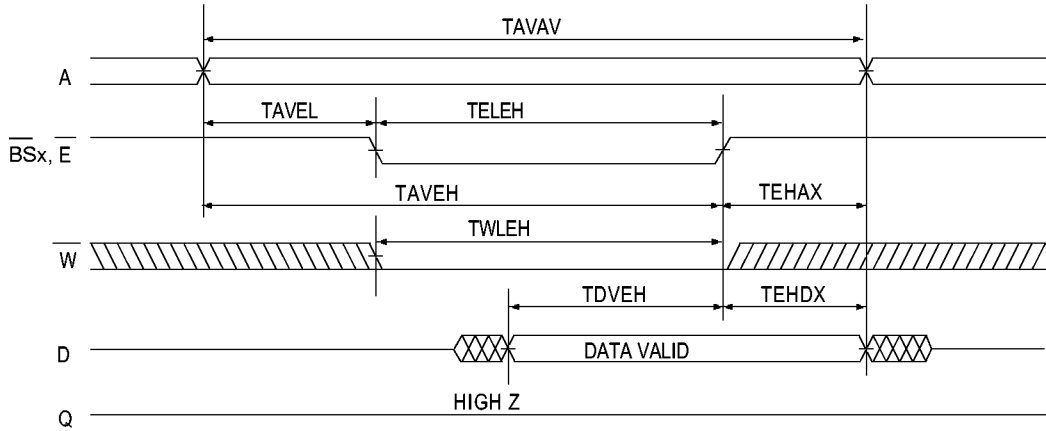
Parameter	Symbol		12ns		15ns		20ns	
	JEDEC	Alt.	Min	Max	Min	Max	Min	Max
Write Cycle Time	TAVAV	TWC	12		15		20	
Chip Enable to End of Write	TELWH	TCW	8		9		15	
	TELEH	TCW	8		9		15	
Byte Select to End of Write	TBLWH	TBW	8		9		15	
Address Setup Time	TAVWL	TAS	0		0		0	
Address Valid to End of Write	TAVEL	TAS	0		0		0	
	TAVWH	TAW	9		10		15	
Write Pulse Width	TAVEH	TAW	9		10		15	
	TWLWH	TWP	9		10		15	
Write Recovery Time	TWLEH	TWP	9		10		15	
	TWHAX	TWR	0		0		0	
Data Hold Time	TEHAX	TWR	0		0		0	
	TWHDX	TDH	0		0		0	
Write to Output in High Z (1)	TWLQZ	TWHZ	0	5	0	6	0	7
	TDVWH	TDW	5		6		8	
Data to Write Time	TDVEH	TDW	5		6		8	
	TWHQX	TWLZ	2		2		2	

Note 1: Parameter guaranteed, but not tested.

### Write Cycle 1 - W Controlled



**Write Cycle 2 -  $\bar{E}$  Controlled**



### Ordering Information

#### Commercial (0°C to +70°C)

Part Number	Speed (ns)	Package No.
ED18LM32257V12AC	12	99
ED18LM32257V15AC	15	99
ED18LM32257V20AC	20	99

#### Industrial (-40°C to +85°C)

Part Number	Speed (ns)	Package No.
ED18LM32257V15AI	15	99
ED18LM32257V20AI	20	99

#### Military (-55°C to +125°C)

Part Number	Speed (ns)	Package No.
ED18LM32257V15AM	15	99
ED18LM32257V20AM	20	99

### Package Description

Package No. 99

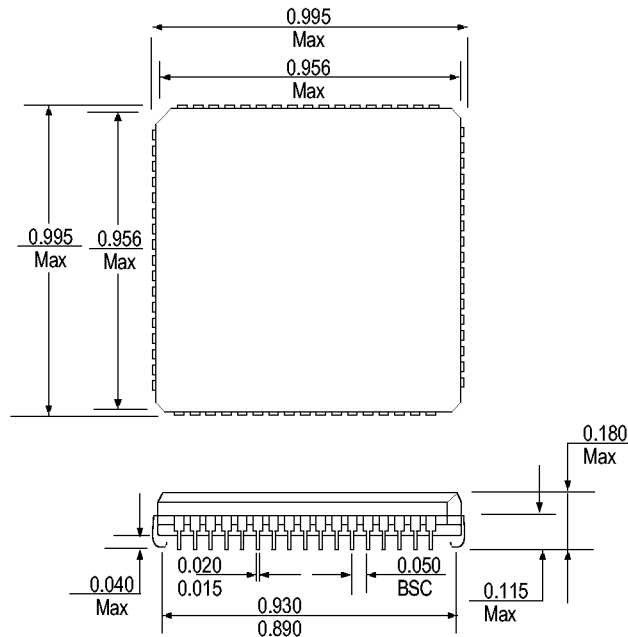
68 Lead PLCC

JEDEC MO-47AE

Theta Ja = 40°C/W

Theta Jc = 15°C/W

Weight = 4.2g



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